

## SILICON MIXER DIODE

### DESCRIPTION:

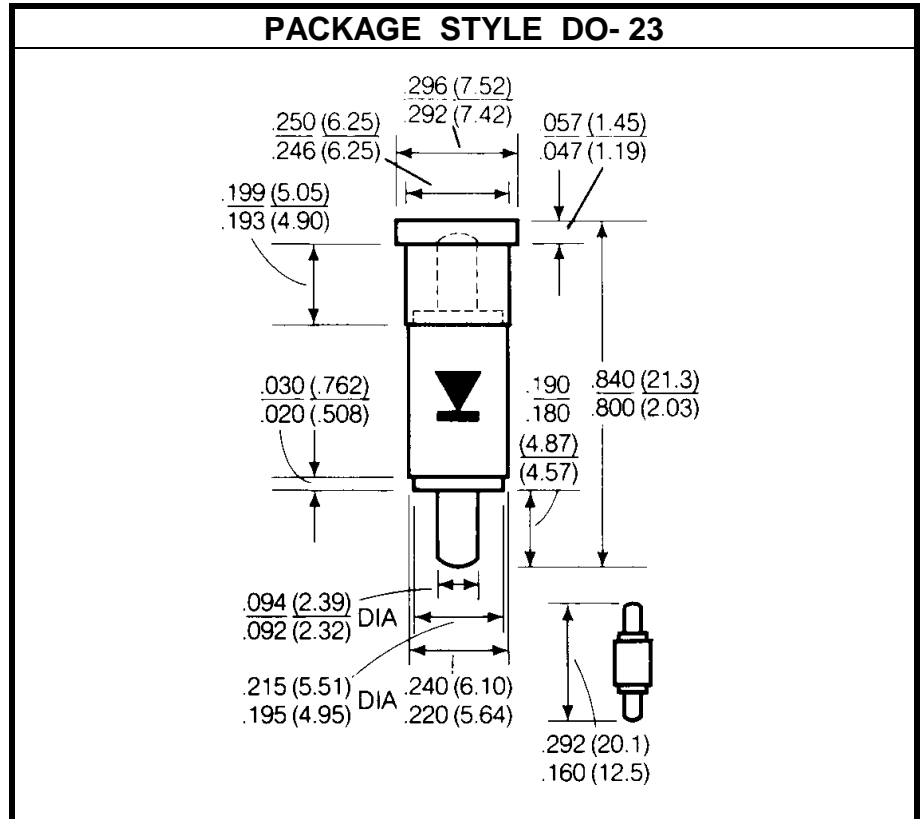
The **ASI 1N415E** is a Silicon Mixer Diode Designed for Applications Operating From 8.0 to 12.4 GHz.

### FEATURES:

- High burnout resistance
- Low noise figure
- Hermetically sealed package

### MAXIMUM RATINGS

$I_F$	20 mA
$V_R$	1.0 V
$P_{DISS}$	2.0 (ERGS) @ $T_C = 25\text{ }^\circ\text{C}$
$T_J$	-55 $^\circ\text{C}$ to +150 $^\circ\text{C}$
$T_{STG}$	-55 $^\circ\text{C}$ to +150 $^\circ\text{C}$



### CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIM	UNITS
$N_F$	$F = 9375\text{ MHz}$ $R_L = 100\ \Omega$ $P_{I_0} = 1.0\text{ mW}$ $I_F = 30\text{ MHz}$ $N_{Fif} = 1.5\text{ dB}$			7.5	dB
$V_{SWR}$				1.3	
$Z_{IF}$	$R_L = 22\ \Omega$ $f = 1000\text{ Hz}$	335		465	$\Omega$
frange		8.0		12.4	GHz